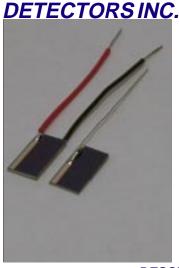
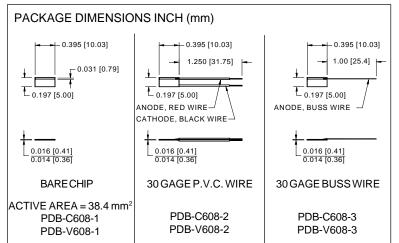
# **PHOTONIC** Silicon Photodiode, Blue Enhanced Solderable Chips

Photoconductive Type PDB-C608 Photovoltaic Type PDB-V608





### **FEATURES**

- Blue enhanced
- Photovoltaic type
- Photoconductive type
- High quantum efficiency

### DESCRIPTION: Low cost blue enhanced planar diffused

silicon solderable photodiode. The  ${\bf PDB\text{-}V608}$  cell is designed for low noise, photovoltaic applications. The  ${\bf PDB\text{-}C608}$  cell is

designed for low capacitance, high speed, photoconductive operation. They are available bare, PVC or buss wire leads.

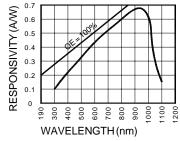
#### **APPLICATIONS**

- Optical encoder
- Position sensor
- Industrial controls
- Instrumentation

#### ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

| SYMBOL           | PARAMETER .                 | PDB- | C608 | PDB- | V608 | UNITS |  |
|------------------|-----------------------------|------|------|------|------|-------|--|
| 01111202         |                             | MIN  | MAX  | MIN  | MAX  | 00    |  |
| VBR              | Reverse Voltage             |      | 75   |      | 25   | V     |  |
| T <sub>STG</sub> | Storage Temperature         | -40  | +125 | -40  | +125 | °C    |  |
| То               | Operating Temperature Range | -40  | +100 | -40  | +100 | ∘C    |  |
| Ts               | Soldering Temperature       |      | +224 |      | +224 | °C    |  |
| I <sub>L</sub>   | Light Current               |      | 500  |      | 500  | mA    |  |

## SPECTRAL RESPONSE



#### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

| SYMBOL | CHARACTERISTIC             | TESTCONDITIONS                   | PDB-C608                    |     |                           | PDB-V608 |      |        | LINITO  |
|--------|----------------------------|----------------------------------|-----------------------------|-----|---------------------------|----------|------|--------|---------|
|        |                            |                                  | MIN                         | TYP | MAX                       | MIN      | TYP  | MAX    | UNITS   |
| Isc    | Short Circuit Current      | H = 100 fc, 2850 K               | 455                         | 475 |                           | 455      | 475  |        | $\mu$ A |
| ΙD     | Dark Current               | H = 0, V <sub>R</sub> = 5 V*     |                             | 25  | 50                        |          | 40   | 80     | nA      |
| Rsн    | Shunt Resistance           | H = 0, V <sub>R</sub> = 10 mV    | 5                           | 10  |                           | 8        | 20   |        | MΩ      |
| TC RsH | RsH Temp. Coefficient      | H = 0, V <sub>R</sub> = 10 mV    |                             | -8  |                           |          | -8   |        | %/°C    |
| CJ     | Junction Capacitance       | H = 0, V <sub>R</sub> = 5 V**    |                             | 200 |                           |          | 5000 |        | pF      |
| λrange | Spectral Application Range | Spot Scan                        | 350                         |     | 1100                      | 350      |      | 1100   | nm      |
| λр     | Spectral Response - Peak   | Spot Scan                        |                             | 940 |                           |          | 940  |        | nm      |
| VBR    | Breakdown Voltage          | I = 10 μA                        | 25                          | 50  |                           | 5        | 15   |        | V       |
| NEP    | Noise Equivalent Power     | V <sub>R</sub> = 0 V @ Peak      | 2.5 x 10 <sup>-13</sup> TYP |     | 1 x 10 <sup>-13</sup> TYP |          |      | W/ √Hz |         |
| tr     | Response Time              | RL = 1 KΩ V <sub>R</sub> = 5 V** |                             | 28  |                           |          | 1200 |        | nS      |

<sup>\*</sup>VR = 100 mV on Photovoltaic type \*\*VR = 0 V on Photovoltaic type